



INFORMATION DISCLOSURE

STATEMENT BY APPLICANT

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Attorney Docket Number

41994/JWP/C766

Application Number

09/895,791

Filing Date

June 29, 2001

Applicant(s)

Richard C. Flagan, et al.

Group Art Unit

1762

Examiner Name

to be assigned

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	Cite No. ¹	DOCUMENT NUMBER Number - kind code ² . (If known)	PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE
RB		6,090,666	07-18-2000	Ueda et al.

TC 1700

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EXAMINER INITIALS	Cite No. ¹	Foreign Patent Document Country Code ³ - Number ⁴ . Kind Code ⁵ (If known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	T ⁶ (✓)
RB		JP 11 111867	04-23-1999	Sharp Corp	X

OTHER DOCUMENTS

EXAMINER INITIALS	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
RB	✓	PCT International Search Report dated March 1, 2002 from corresponding PCT application No. PCT/US01/20829 filed June 29, 2001
	✓	PCT International Search Report dated March 1, 2002 from PCT application No. PCT/US01/20827 filed June 29, 2001
	✓	BINNIG, G. et al.; <i>Atomic Force Microscope</i> ; Physical Review Letters; March 3, 1986; Volume 56, Number 9; pp. 930-933
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RB	✓	DUTTA, Amit et al.; <i>Electron Transport in Nanocrystalline Si Based Single Electron Transistors</i> ; Jpn. J. Appl. Phys.; July 2000; Vol. 39; pp. 4647-4650

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<i>Richard A. ...</i>	5/19/03

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RG	✓	DUTTA, Amit et al.; <i>Fabrication and Electrical Characteristics of Single Electron Tunneling Devices Based on Si Quantum Dots Prepared by Plasma Processing</i> ; Jpn. J. Appl. Phys.; June 1997; Vol. 36; pp 4038-4041
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	✓	HAMAKER, H.C.; <i>The London - Van Der Waals Attraction Between Spherical Particles</i> ; Physica IV, November 23, 1937; No. 10; pp. 1058-1072
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	✓	LEFF, Daniel V. et al.; <i>Thermodynamic Control of Gold Nanocrystal Size: Experiment</i>

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	✓	LITTAU, K.A. et al.; <i>A Luminescent Silicon Nanocrystal Colloid via a High-Temperature Aerosol Reaction</i> ; 1993; Vol. 97; pp. 1224-1230; J. Phys. Chem
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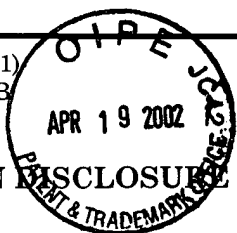
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	✓	WU, Jin Jwang et al.; <i>A Method for the Synthesis of Submicron Particles</i> ; Langmuir; 1987; Vol. 3, pp. 266-271
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	✓	ZHANG, Shou-Hua et al.; <i>Radial Differential Mobility Analyzer</i> ; Aerosol Science and Technology; 1995; Vol. 23; pp. 357-372
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